

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.079DV1 C I	APPLICATION NO. <del>08/079,004</del> unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (USE SEVERAL SHEETS IF NECESSARY)	APPLICANT Gonzalez et al.	
	FILING DATE <del>June 12, 2004</del> Herewith	GROUP Unknown

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
BK		6,033,898	03/07/00	Aronowitz et al.			03/09/98
J		6,037,224	03/14/00	Buller et al.			05/02/97
✓		6,110,842	08/28/00	Okuno et al.			04/22/98

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073101

EXAMINER <i>John K. Kuhl</i>	DATE CONSIDERED <i>2/11/05</i>
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	

FORM PYO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON 67894-079&VICI	APPLICATION NO. Unknown
INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Gonzalez et al.	
		FILING DATE Herewith	GROUP Unknown

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)	
<i>pb</i>	4,827,153	12/9/86	Masuoka				
	4,651,406	3/24/87	Shimizu et al.				
	4,957,878	9/18/90	Lowrey et al.				
	4,675,982	6/30/87	Noble, Jr. et al.				
	5,057,449	10/15/91	Lowrey et al.				
	5,264,724	11/23/93	Brown et al.				
	5,358,894	10/25/94	Fazan et al.				
	5,360,769	11/1/94	Thakur et al.				
	5,376,593	12/27/94	Sandhu et al.				
	5,393,683	2/28/95	Mathews et al.				
	5,405,791	4/11/95	Ahmad et al.				
	5,407,870	4/18/95	Okada et al.				
	5,483,234	10/31/95	Toriumi et al.				
	5,502,009	3/28/96	Lin				
	5,668,035	9/16/97	Fang et al.				
	5,663,819	1/26/99	Gonzalez				
	5,966,618	10/12/99	Sun et al.				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	S. Shimizu, et al., "Impact of Surface Proximity Gettering and Nitrided Oxide Side-Wall Spacer by Nitrogen Implantation on Sub-Quarter Micron CMOS LDD FETs," IEDM 1995, pp. 859-862

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061101

EXAMINER <i>John A. Sal</i>	DATE CONSIDERED <i>2/11/05</i>
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	